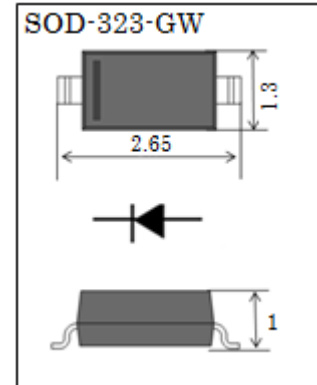


Small Signal Diode / DATA SHEET

1N4148WX, 1N4448WX, 1N914BWX

- ◇ General purpose diodes
- ◇ Fast switching devices
- ◇ **SOD323 Thin** SMD package
- ◇ RoHS compliant / Green EMC
- ◇ Matte Tin (Sn) Lead finish
- ◇ Cathode Band / Device marking

Device Marking Code	
1N4148WX	T4
1N4448WX	T5
1N914BWX	S3



Absolute Maximum Ratings (Ta = 25 °C)

Symbol	Parameter	Value	Units
V_{RSM}	Non-Repetitive Peak Reverse Voltage	100	V
V_{RRM}	Repetitive Peak Reverse Voltage	75	V
I_{FRM}	Repetitive Peak Forward Current	300	mA
I_{FSM}	Non-Repetitive Peak Forward Current *1	2	A
I_O	Continuous Forward Current	150	mA
P_D	Power Dissipation	200	mW
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	-55 to +150	°C

*1 Pulse width = 1 μ s

Electrical Characteristics (Ta = 25 °C)

Symbol	Parameter	Conditions	Min	Max	Units
BV_R	Breakdown Voltage	$I_R = 100 \mu A$	100		V
		$I_R = 5 \mu A$	75		V
I_R	Reverse Current	$V_R = 20V$		25	nA
		$V_R = 75V$		5	μA
V_F	Forward Voltage	$I_F = 5mA$ *2	0.62	0.72	V
		$I_F = 10mA$		1	V
		$I_F = 100mA$ *2		1	V
C	Capacitance	$V_R = 0V, f = 1MHz$		4	pF
T_{RR}	Reverse Recovery Time	$I_F = 10mA, V_R = 6V$ $I_{RR} = 1mA, R_L = 100 \Omega$		4	ns

*2 Excluded 1N4148WS

Characteristics Curves

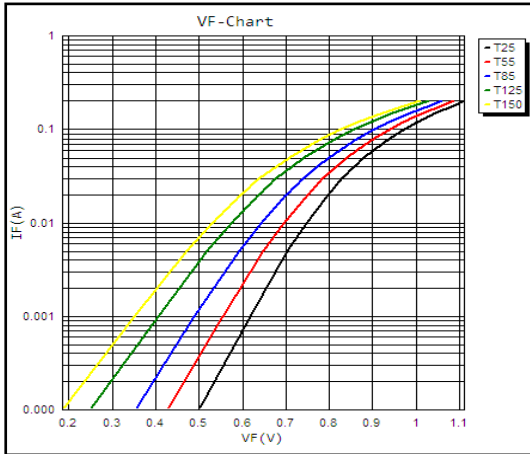


Fig.2 Forward current(IF) vs Forward voltage(VF)

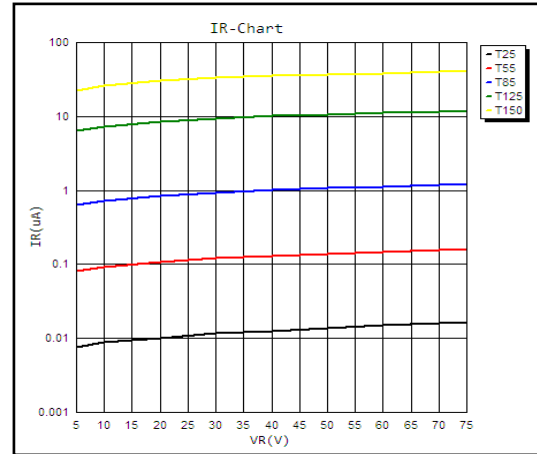


Fig.3 Reverse current(IR) vs Reverse voltage(VR)

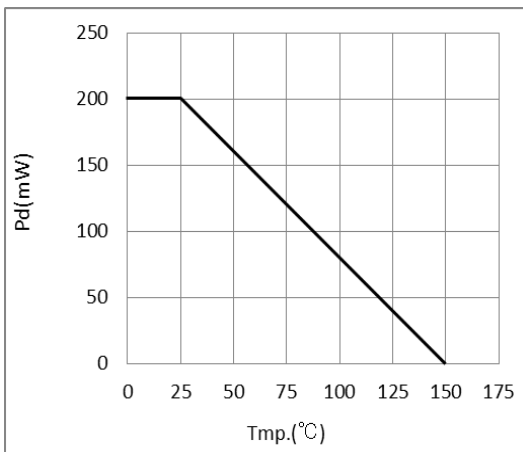


Fig.4 Power Derating Curve

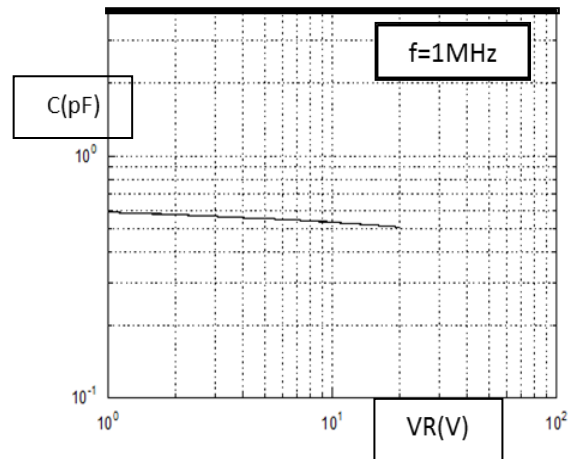


Fig.5 Capacitance vs Reverse voltage(VR)

Ordering Information

Device	Package	Shipping	Tape wide	Emboss pitch	Tape specification	Notes
1N4148WX etc.	SOD323	Tape & Reel 3000pcs /7" Reel	8 mm	4 mm	Conductive	

Package Dimensions

